



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

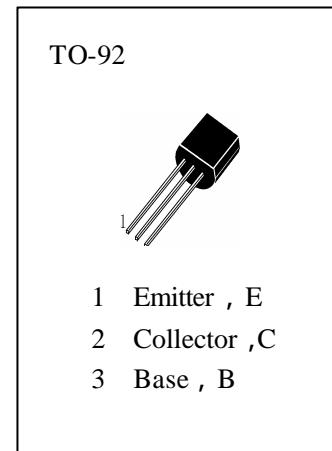
HD882S

AUDIO FREQUENCY POWER AMPLIFIER

LOW SPEED SWITCHING

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation.....	0.75W
V_{CBO} —Collector-Base Voltage.....	40V
V_{CEO} —Collector-Emitter Voltage.....	30V
V_{EBO} —Emitter-Base Voltage.....	5V
I_c —Collector Current.....	3A



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			100	nA	$V_{CB}=30V, I_E=0$
I_{EBO}	Emitter Cut-off Current			100	nA	$V_{EB}=3V, I_C=0$
HFE	DC Current Gain	100		490		$V_{CE}=2V, I_C=1A$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage			0.5	V	$I_C=2 A, I_B=0.2A$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			2.0	V	$I_C=2A, I_B=0.2A$
f_T	Current Gain-Bandwidth Product		80		MHz	$V_{CE}=5V, I_C=0.1A$
C_{ob}	Output Capacitance		55		pF	$V_{CB}=10V, I_E=0, f=1MHz$

h_{FE} Classification

Q

P

E

100—200

160—320

260—490